

L Number	Hits	Search Text	DB	Time stamp
1	164	transistor with gate with spacer with (source drain) with contact	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/18 16:19
2	25975	spacer with contact	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/18 16:20
3	4313	(( spacer with contact) with second	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/18 16:20
4	84	((transistor with gate with spacer with (source drain) with contact) same (( spacer with contact) with second))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/18 16:21
5	94	((transistor with gate with spacer with (source drain) with contact) and @ad<19970331	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/18 16:39
6	54	((transistor with gate with spacer with (source drain) with contact) same (( spacer with contact) with second)) and @ad<19970331	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/18 16:22
7	371763	((thermal\$ heat) with conduct\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/18 16:29
8	6	((transistor with gate with spacer with (source drain) with contact) same ((thermal\$ heat) with conduct\$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/18 16:29
9	40	((transistor with gate with spacer with (source drain) with contact) and @ad<19970331) not (((transistor with gate with spacer with (source drain) with contact) same (( spacer with contact) with second)) and @ad<19970331)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/18 16:39